

CVD Graphene on Silicon Wafer

Product Description

Graphene was successfully grown on single-crystal silicon substrates using metal-free, ambient-pressure chemical vapor deposition. Atomically flat monolayer or bilayer graphene domains, concave bilayer graphene domains, and bulging few-layer graphene domains can be produced by controlling the growth temperature

- Totally customized
- Low and medium volumes
- Any diameter
- Any orientations
- Any thickness

Typical Properties

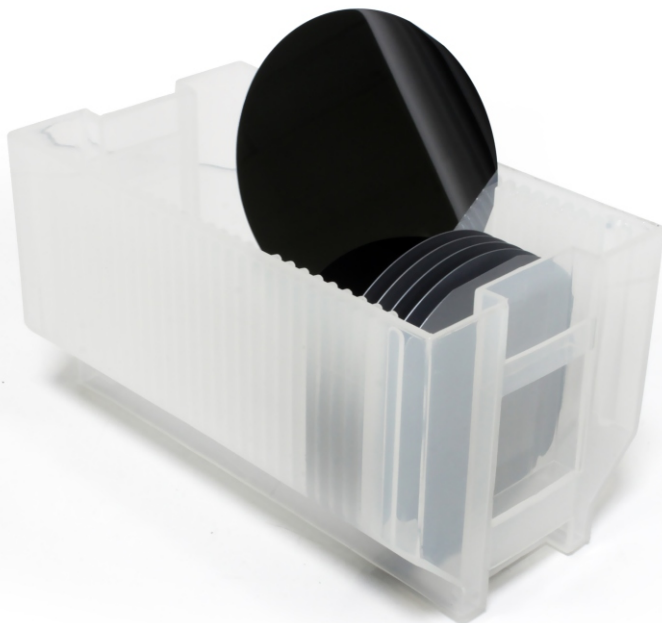
Dopant	:	Graphene
Crystal Orientation	:	< 100>
Type	:	P
Resistivity	:	<600Ω/sq

Applications

- ✓ Graphene electronics and transistors
- ✓ Conductive coatings
- ✓ Aerospace industry applications
- ✓ Support for metallic catalysts
- ✓ Microactuators
- ✓ MEMS and NEMS
- ✓ Chemical and biosensors
- ✓ Multifunctional materials based on graphene
- ✓ IR applications
- ✓ Silicon on sapphire integrated circuit (SOS)
- ✓ Radio frequency integrated circuit (RFIC)

Key Features

Product	:	CVD Graphene on Silicon Wafer
Stock No	:	NS6130-10-1276
CAS	:	7440-21-3
Size	:	1cm x 1cm (CVD Graphene)
Thickness (SiO ₂)	:	300nm



NS6130-10-1276

P
Type

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